

Standard Rectifier

$$V_{RRM} = 2 \times 1200 \text{ V}$$

$$I_{FAV} = 8 \text{ A}$$

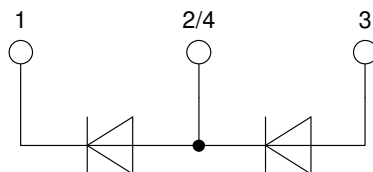
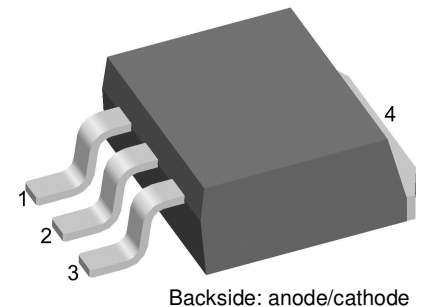
$$V_F = 1.08 \text{ V}$$

Phase leg

Part number

DSP8-12AS

Marking on Product: DSP8-12AS



Features / Advantages:

- Planar passivated chips
- Very low leakage current
- Very low forward voltage drop
- Improved thermal behaviour

Applications:

- Diode for main rectification
- For single and three phase bridge configurations

Package: TO-263 (D2Pak)

- Industry standard outline
- RoHS compliant
- Epoxy meets UL 94V-0

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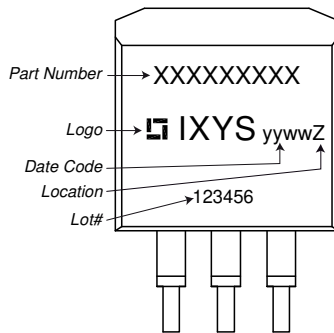


Rectifier				Ratings			
Symbol	Definition	Conditions		min.	typ.	max.	Unit
V_{RSM}	max. non-repetitive reverse blocking voltage					1300	V
V_{RRM}	max. repetitive reverse blocking voltage					1200	V
I_R	reverse current	$V_R = 1200$ V		$T_{VJ} = 25^\circ\text{C}$		10	μA
		$V_R = 1200$ V		$T_{VJ} = 150^\circ\text{C}$		0.2	mA
V_F	forward voltage drop	$I_F = 8$ A		$T_{VJ} = 25^\circ\text{C}$		1.16	V
		$I_F = 16$ A				1.35	V
		$I_F = 8$ A		$T_{VJ} = 150^\circ\text{C}$		1.08	V
		$I_F = 16$ A				1.34	V
I_{FAV}	average forward current	$T_C = 160^\circ\text{C}$		$T_{VJ} = 175^\circ\text{C}$		8	A
		rectangular	d = 0.5				
V_{FO}	threshold voltage			$T_{VJ} = 175^\circ\text{C}$		0.79	V
r_F	slope resistance					30	m Ω
R_{thJC}	thermal resistance junction to case					1.5	K/W
R_{thCH}	thermal resistance case to heatsink				0.25		K/W
P_{tot}	total power dissipation			$T_C = 25^\circ\text{C}$		100	W
I_{FSM}	max. forward surge current	t = 10 ms; (50 Hz), sine		$T_{VJ} = 45^\circ\text{C}$		120	A
		t = 8,3 ms; (60 Hz), sine		$V_R = 0$ V		130	A
		t = 10 ms; (50 Hz), sine		$T_{VJ} = 150^\circ\text{C}$		100	A
		t = 8,3 ms; (60 Hz), sine		$V_R = 0$ V		110	A
I^2t	value for fusing	t = 10 ms; (50 Hz), sine		$T_{VJ} = 45^\circ\text{C}$		72	A ² s
		t = 8,3 ms; (60 Hz), sine		$V_R = 0$ V		70	A ² s
		t = 10 ms; (50 Hz), sine		$T_{VJ} = 150^\circ\text{C}$		50	A ² s
		t = 8,3 ms; (60 Hz), sine		$V_R = 0$ V		50	A ² s
C_J	junction capacitance	$V_R = 400$ V; f = 1 MHz		$T_{VJ} = 25^\circ\text{C}$		4	pF



Package TO-263 (D2Pak)			Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit
I_{RMS}	RMS current	per terminal			25	A
T_{VJ}	virtual junction temperature		-55		175	°C
T_{op}	operation temperature		-55		150	°C
T_{stg}	storage temperature		-55		150	°C
Weight				1.5		g
F_C	mounting force with clip		20		60	N

Product Marking



Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	DSP8-12AS-TRL	DSP8-12AS	Tape & Reel	800	502381
Alternative	DSP8-12AS-TUB	DSP8-12AS	Tube	50	465453

Similar Part	Package	Voltage class
DSP8-12S	TO-263AB (D2Pak) (2)	1200
DSP8-12A	TO-220AB (3)	1200
DSP8-12AC	ISOPLUS220AB (3)	1200
DSP8-08AS	TO-263AA (D2Pak) (3)	800

DSP8-08S	TO-263AB (D2Pak) (2)	800
DSP8-08A	TO-220AB (3)	800

Equivalent Circuits for Simulation

** on die level*

$T_{VJ} = 175^{\circ}\text{C}$

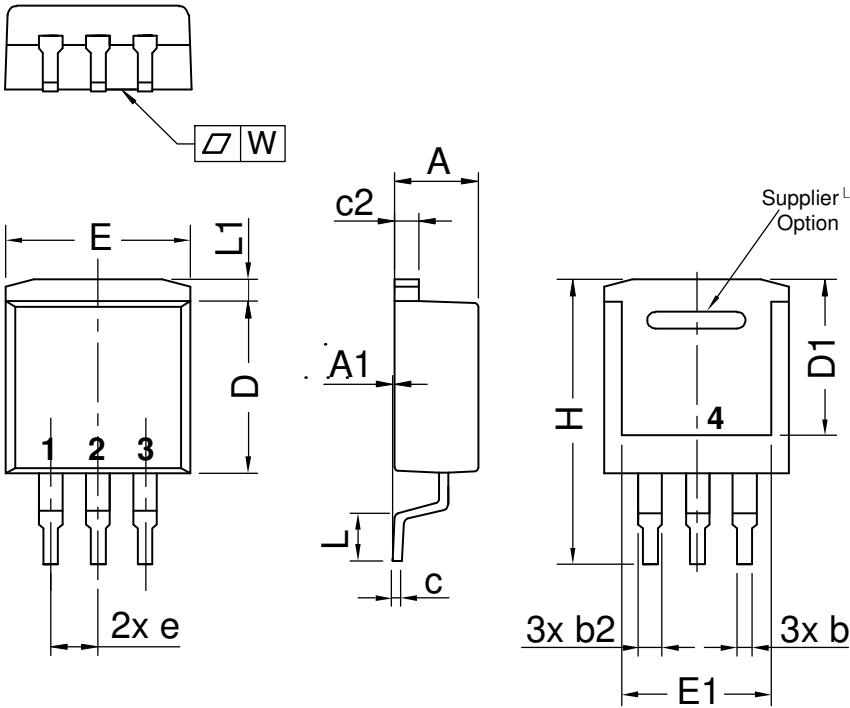


Rectifier

$V_{0\ max}$	threshold voltage	0.79	V
$R_{0\ max}$	slope resistance *	30	mΩ

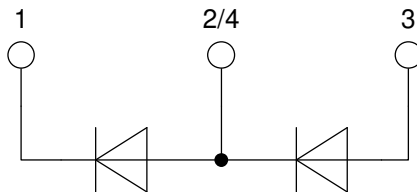


Outlines TO-263 (D2Pak)



Dim.	Millimeter		Inches	
	min	max	min	max
A	4.06	4.83	0.160	0.190
A1	typ. 0.10		typ. 0.004	
A2	2.41		0.095	
b	0.51	0.99	0.020	0.039
b2	1.14	1.40	0.045	0.055
c	0.40	0.74	0.016	0.029
c2	1.14	1.40	0.045	0.055
D	8.38	9.40	0.330	0.370
D1	8.00	8.89	0.315	0.350
D2	2.5		0.098	
E	9.65	10.41	0.380	0.410
E1	6.22	8.50	0.245	0.335
e	2,54 BSC		0,100 BSC	
e1	4.28		0.169	
H	14.61	15.88	0.575	0.625
L	1.78	2.79	0.070	0.110
L1	1.02	1.68	0.040	0.066
W	typ. 0.02	0.040	typ. 0.0008	0.002

All dimensions conform with and/or within JEDEC standard.



Rectifier


Fig. 1 Forward current versus voltage drop per diode

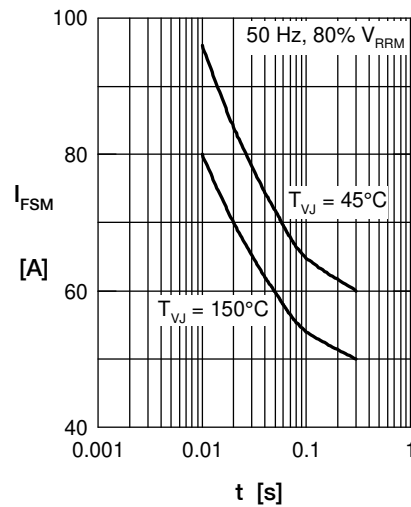


Fig. 2 Surge overload current

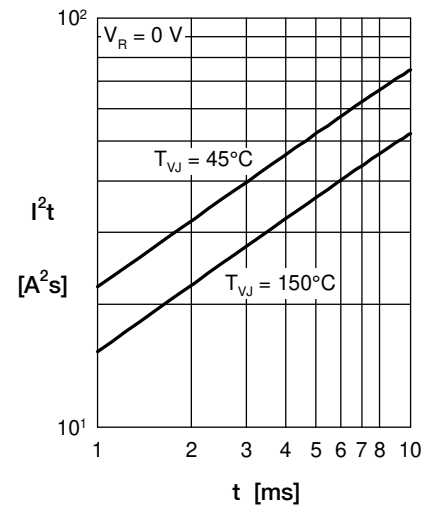
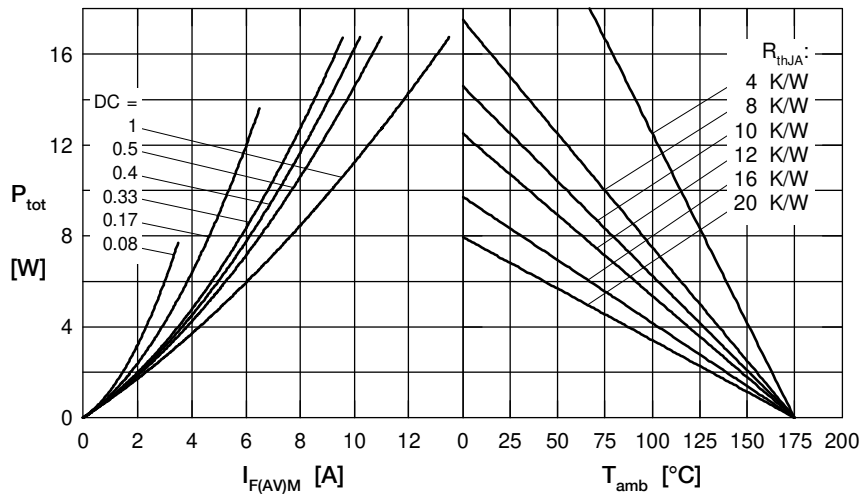

 Fig. 3 I^2t versus time per diode


Fig. 4 Power dissipation vs. direct output current and ambient temperature

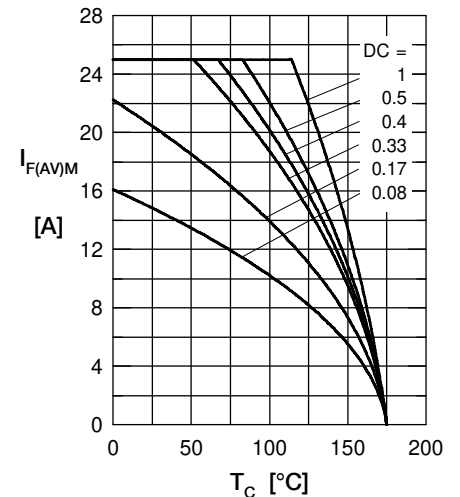


Fig. 5 Max. forward current vs. case temperature

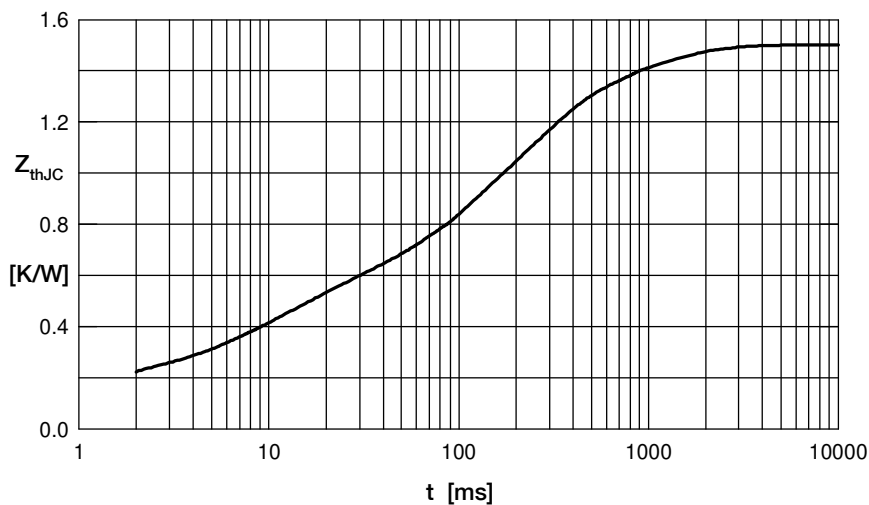


Fig. 6 Transient thermal impedance junction to case

 Constants for Z_{thJC} calculation:

i	R_{thi} (K/W)	t_i (s)
1	0.155	0.0005
2	0.332	0.0095
3	0.713	0.17
4	0.3	0.8
5	0.00001	0.00001